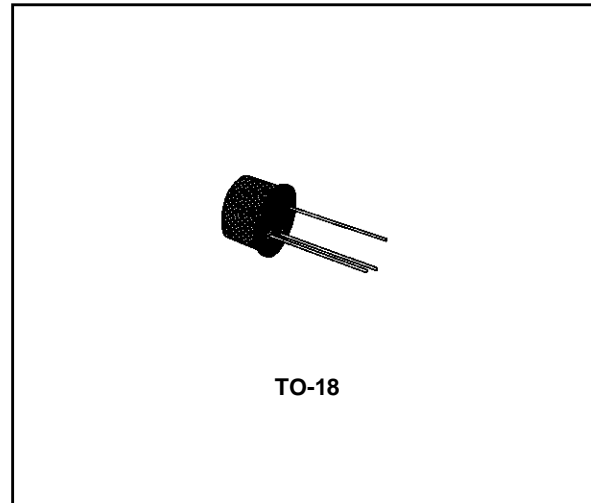


HIGH VOLTAGE AMPLIFIER

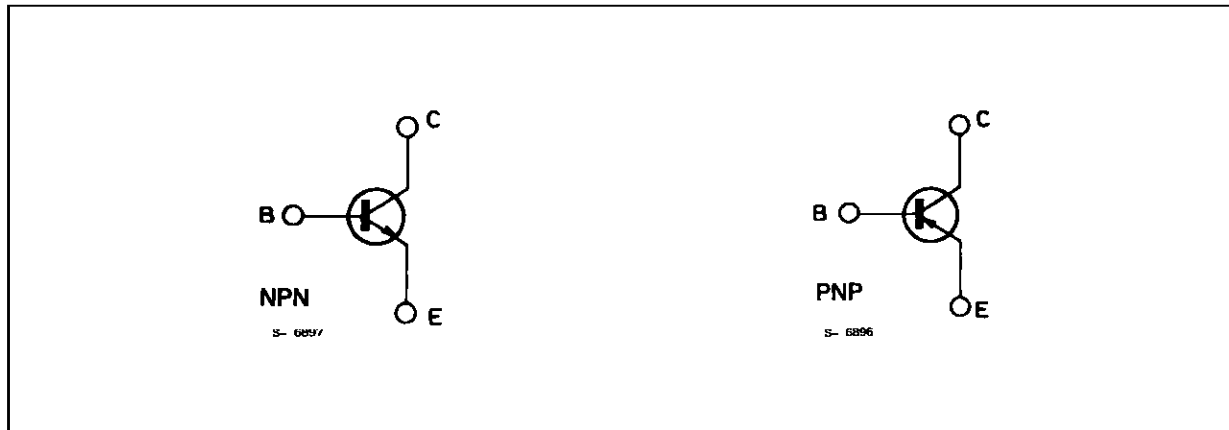
DESCRIPTION

The BC394 is a silicon planar epitaxial NPN transistor in Jedec TO-18 metal case, designed for general purpose high-voltage and video amplifier applications.

The complementary PNP type is the BC393.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	180	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	180	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	6	V
I_C	Collector Current	100	mA
P_{tot}	Total Power Dissipation at $T_{amb} \leq 25\text{ }^\circ\text{C}$ at $T_{case} \leq 25\text{ }^\circ\text{C}$	0.4	W
		1.4	W
T_{stg}	Storage Temperature	- 55 to 200	$^\circ\text{C}$
T_j	Junction Temperature	200	$^\circ\text{C}$

BC394

THERMAL DATA

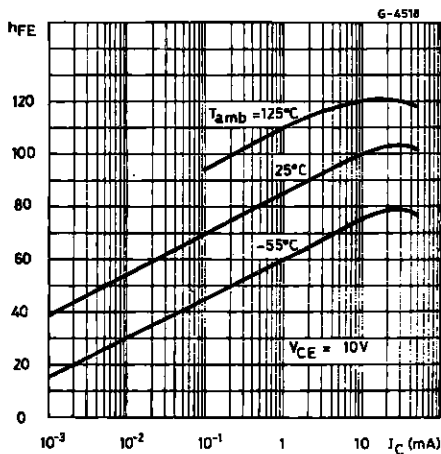
$R_{th j-case}$	Thermal Resistance Junction-case	Max	125	$^{\circ}C/W$
$R_{th j-amb}$	Thermal Resistance Junction-ambient	Max	440	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$ unless otherwise specified)

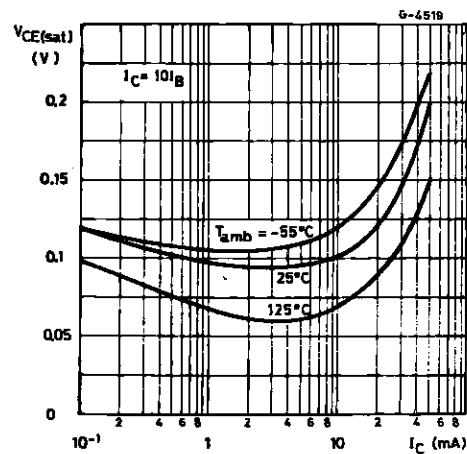
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = 100 V$ $V_{CB} = 100 V$ $T_{amb} = 150^{\circ}C$			50 50	nA μA
$V_{(BR) CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 100 \mu A$	180			V
$V_{(BR) CEO}^*$	Collector-emitter Breakdown Voltage ($I_B = 0$)	$I_C = 10 mA$	180			V
$V_{(BR) EBO}$	Emitter-base Breakdown Voltage ($I_C = 0$)	$I_E = 100 \mu A$	6			V
$V_{CE (sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 10 mA$ $I_B = 1 mA$ $I_C = 50 mA$ $I_B = 5 mA$		200 400	300	mV mV
$V_{BE (sat)}^*$	Base-emitter Saturation Voltage	$I_C = 10 mA$ $I_B = 1 mA$ $I_C = 50 mA$ $I_B = 5 mA$		750 850	900	mV mV
h_{FE}^*	DC Current Gain	$I_C = 1 mA$ $V_{CE} = 10 V$ $I_C = 10 mA$ $V_{CE} = 10 V$	30	85 100		
f_T	Transition frequency	$I_C = 10 mA$ $V_{CE} = 10 V$	50	95		MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $V_{CB} = 10 V$ $f = 1 MHz$		5		pF

* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.

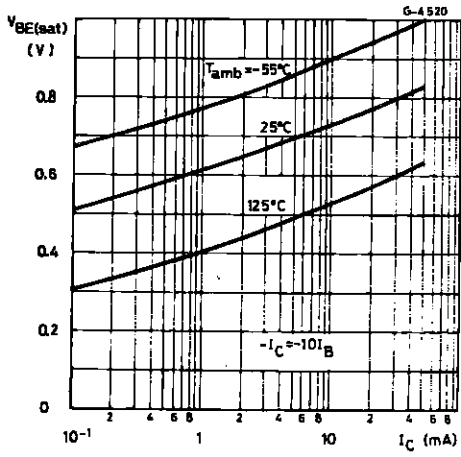
DC Current.



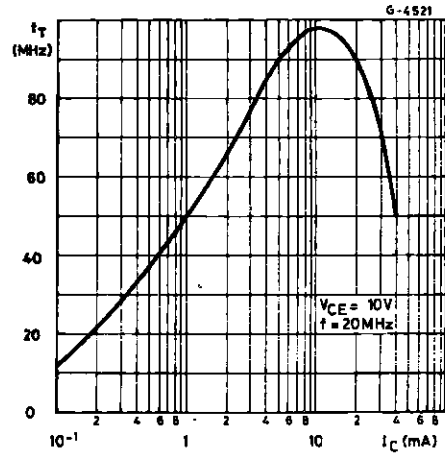
Collector-emitter Saturation Voltage.



Base-emitter Saturation Voltage.

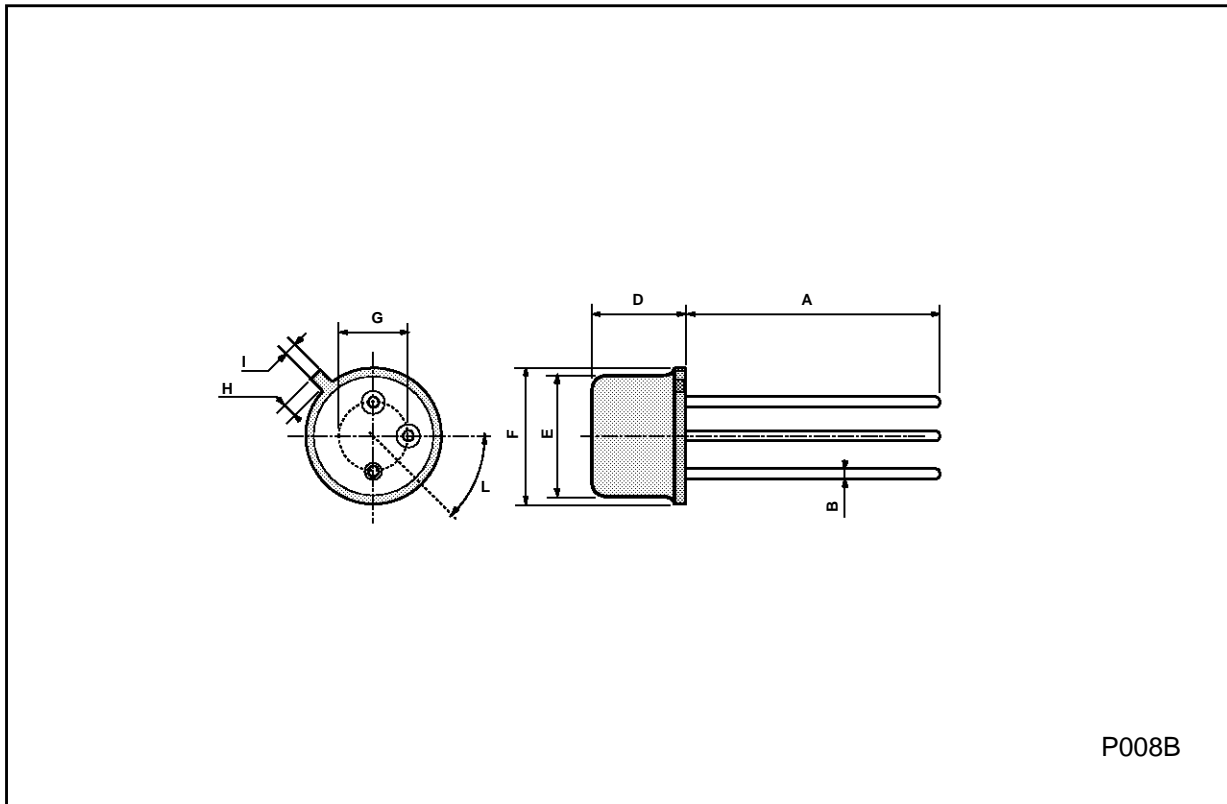


Transition Frequency.



TO39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

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